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**PATENT APPLICATION**

**FILING UNDER 37 CFR §1.312  
EXPEDITED PROCEDURE  
TECHNOLOGY CENTER ART UNIT 1722**

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re the Application of	ATTN: OFFICE OF PUBLICATIONS
Izumi FUSEGAWA et al.	Notice of Allowance Mailed 09/25/07 - Batch/Confirmation No. 5592
Application No.: 10/568,186	Group Art Unit: 1722
Filed: February 13, 2006	Examiner: F. HITESHEW
	Docket No.: 126961
For: METHOD FOR PRODUCING A SINGLE CRYSTAL AND SILICON SINGLE CRYSTAL WAFER	

**COMMENTS ON STATEMENT OF REASONS FOR ALLOWANCE**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

In reply to the Examiner's Statement of Reasons for Allowance in the Notice of Allowance mailed September 25, 2007, please consider the following remarks.

The Examiner's Statement for Reasons for Allowance states: "the most relevant prior art or reference cited was that of Mitamura et al. in view of W0 01/81661 A1." However, Applicants argued that Mitamura et al. cannot be used as a prior art reference. Secondly, in the Reasons for Allowance at page 2, paragraph 2, line 5, the term "downward" is included as a feature of the claimed invention. However, claim 7, nor any other allowed claim, includes the feature "downward." Applicants respectfully request a corrected or supplemental Notice of Allowance with the indicated corrections.

The Examiner is invited to contact the undersigned at the telephone number set forth below regarding any matter concerning this application.

Respectfully submitted,



William P. Berridge  
Registration No. 30,024

Andrew B. Freistein  
Registration No. 52,917

JAO:ABF/hms

Date: November 5, 2007

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**Telephone: (703) 836-6400**

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